## Gate Delay Estimation in STA under Dynamic Power Supply Noise

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### Overview

- Background & Motivation
- Conventional methods to cope w/ noise on timing
  - Guard-banding based on Static IR-Drop Analysis
  - Gate delay estimation considering noise waveform
- Evaluation of conventional estimation method at 45nm
- Proposed method to improve the estimation accuracy
- Evaluation results of the proposed method
- Conclusion



## What is Power/Ground Noise?



Power/Ground Noise

- Temporal P/G level fluctuation due to simultaneous signal switching.
  →May cause timing failure.
- So far, guard-banding based on static IR-drop analysis.
- Recently, dynamic voltage drop analysis tools are introduced.
  - Reduce peak voltage drop by proper placement of decoupling cells.

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## **Technology Trends**



W/ Process technology scaling

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- Current density 1, Wire resistance 1
- Power supply voltage \$\overline\$, Non-linearity of voltage-delay characteristics \$\overline\$
- Noise amplitude unchanged despite technology scaling [A.Mezhiba, IEEE Trans. on VLSI '04]

 $\rightarrow$  Concern about timing failure becomes more serious.  $\uparrow$ 

## Static IR-Drop Analysis and It's Limitation

Express path delay fluctuation as follows

$$\Delta v_i = \frac{1}{T_i - T_{i-1}} \int_{T_{i-1}}^{T_i} \Delta v \, dt$$

$$\Delta D_{path} = \sum_{i=1}^{n} \Delta D_{i} = \sum_{i=1}^{n} \frac{\partial D_{i}}{\partial v} \Delta v_{i}$$

where *n*: # of stages,  $\Delta v(t)$ : noise waveform,  $D_i: i_{th}$  stage delay,  $T_i$ : arrival time of  $i_{th}$  gate output,  $\partial D_i / \partial v: i_{th}$  stage delay sensitivity to voltage.

Approximate the sensitivity by m<sub>th</sub> order polynomial and assume uniformity.

$$\frac{\partial D_i}{\partial v} = a_{0i} + \sum_{j=1}^m a_{ji} \cdot \Delta v_i^j$$
$$\Delta D_{path} = a_0 \int_{T_0}^{T_n} \Delta v \, dt + O(\Delta v^2)$$



 $\rightarrow$  Delay estimation by static IR-Drop analysis gives a reasonable approximation, only for setup critical path with insignificant sensitivity difference of each stage.

## Conventional Gate Delay Estimation Method



- Gate delay estimation considering noise waveform at 180nm node.
  - Based on Eq. DC voltage approach.
  - Classify the fluctuations into following two cases.
    - Stage delay increase in *Current Change Case*
    - Stage delay **decrease** in *Charge Change Case*
- $\rightarrow$ Evaluate at 45nm node and improve the accuracy if needed.

## Review of Current Change Case



- Corresponds to rising transition under power supply noise.
- Stage delay increase since charging current becomes less.
- Eq. DC voltage is heuristically determined by averaging the noise between 0%-60% period of output waveform at an ideal voltage.

## Review of Charge Change Case



- Corresponds to falling transition under power supply noise.
- Stage delay decreases since output voltage is dropped in prior to the transition.
- Obtain starting voltage from output response to power supply noise.

## Experimental circuit



- Use triangular signal as a noise waveform.
- Sweep noise injection time within path timing window to obtain stage delay fluctuations.

Evaluate the computed results against the SPICE reference.



#### Evaluation of conventional method at 45nm node



Current Change Case: X1, X3

The **tendencies** of stage delay increase differ from the references.

 $\rightarrow$ Need to revise an averaging interval to obtain Eq. DC voltage.

Charge Change Case: X2, X4

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There exists both **delay increase region** as well as decrease region.

#### Improve the estimation of *Current Change Case*



Conventional method assumes linearity of voltage-delay characteristics and small fluctuation.

Need to consider non-linearity in recent technologies.

 $\rightarrow$  Iteratively find T<sub>i</sub> satisfying T<sub>i</sub> - T<sub>i-1</sub> = D<sub>i</sub> +  $\Delta$ D<sub>i</sub>.

#### Improve the estimation of *Charge Change Case*



An example of delay increase in *Charge Change Case*. Delay increase due to NMOS  $V_{gs}$  reduction.

- Since PMOS is already OFF, delay increase originates from a temporal NMOS V<sub>gs</sub> reduction.
- Apply the iterative procedure as well as the *Current Change Case* with **delay sensitivity to gate input voltage** instead of supply voltage dependence.
- The stage delay decrease is estimated before the increase is estimated and both cases are considered.

#### Why was increase in *Charge Change Case* missed?



Stage delay fluctuation of 10 stages inverter chain at 180nm node.

- Stage delay increase in *Charge Change Case* is negligibly small at 180nm node.
- Emerged since noise amplitude and over-drive voltage  $(V_{dd}-V_{th})$  become comparable.

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#### Improved estimation results



- The estimations are improved considering following factors.
  - Non-linearity of voltage-delay characteristics.
  - Decrease in over-drive voltage  $(V_{dd}-V_{th})$ .

#### Evaluation of proposed method



- Evaluate average error and standard deviation for each randomlygenerated circuit.
- Compare averaging voltage within path delay (setup critical case with static-IR-drop analysis), conventional, and proposed.

#### **Evaluation results**



- Delay fluctuation due to noise is 8.2% on average.
- Error is improved to 1.4% by guard-banding of Static IR-Drop.
- Errors of conventional and proposed which consider dynamic noise waveform are 2.0% and 0.61%, respectively.

New estimation factors need to be considered in recent technologies.

## Conclusion

Timing estimation based on static IR-drop analysis gives an optimistic results in the cases where,

Short delay path

Significant delay sensitivity difference to voltage of each stage.

- Following factors need to be considered in the recent techs. in addition to the conventional method proposed at 180nm node.
  - Non-linearity of voltage-delay characteristics

Decrease in over-drive voltage.

Errors in experimental circuits are reduced from 8% to 2%.



# Thank You

